



## GaAs MMIC 1 WATT POWER AMPLIFIER DC - 6 GHz

### Typical Applications

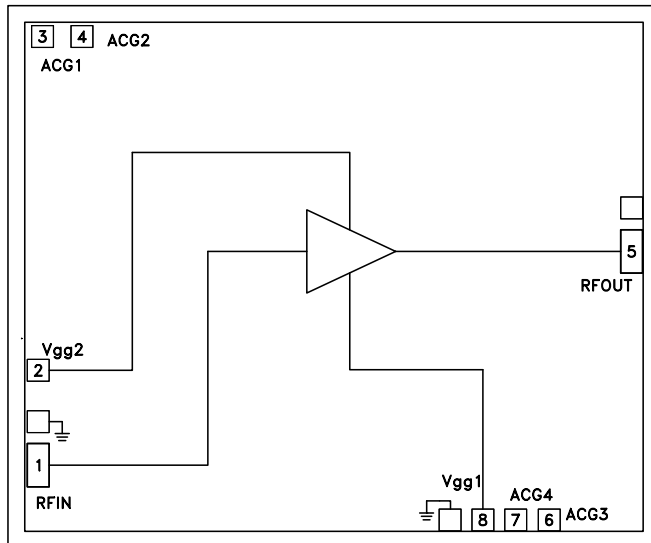
The HMC637A is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation
- Fiber Optics

### Features

- P1dB Output Power: +30.5 dBm
- Gain: 14 dB
- Output IP3: +41 dBm
- Bias Supplies: +12V, +6V, -1V
- 50 Ohm Matched Input/Output
- Die Size: 2.98 x 2.48 x 0.1 mm

### Functional Diagram



### General Description

The HMC637A is a GaAs MMIC MESFET Distributed Power Amplifier die which operates between DC and 6 GHz. The amplifier provides 14 dB of gain, +41 dBm output IP3 and +30.5 dBm of output power at 1 dB gain compression while requiring 400mA from a +12V supply. Gain flatness is excellent at  $\pm 0.5$  dB from DC to 6 GHz making the HMC637A ideal for EW, ECM, Radar and test equipment applications.

The HMC637A amplifier I/Os are internally matched to 50 Ohms facilitating integration into Multi-Chip-Modules (MCMs). All data is taken with the chip connected via two 0.025mm (1 mil) wire bonds of minimal length 0.31 mm (12 mils).

### Electrical Specifications, $T_A = +25^\circ\text{C}$ , $V_{dd} = +12\text{V}$ , $V_{gg2} = +6\text{V}$ , $I_{dd} = 400\text{mA}$ <sup>[1]</sup>

Parameter	Frequency	Min.	Typ.	Max.	Units
Gain	DC - 6.0 GHz	11	14		dB
Gain Flatness	DC - 6.0 GHz		$\pm 0.5$		dB
Gain Variation Over Temperature	DC - 6.0 GHz		0.008		dB/°C
Input Return Loss	DC - 6.0 GHz		14		dB
Output Return Loss	DC - 6.0 GHz		18		dB
Output Power for 1 dB Compression (P1dB)	DC - 6.0 GHz		30.5		dBm
Saturated Output Power (Psat)	DC - 6.0 GHz		31.5		dBm
Output Third Order Intercept (IP3) <sup>[2]</sup>	DC - 6.0 GHz		43		dBm
Noise Figure	DC - 2 GHz 2.0 - 6.0 GHz		12 4		dB dB
Supply Current (Idd)			400		mA

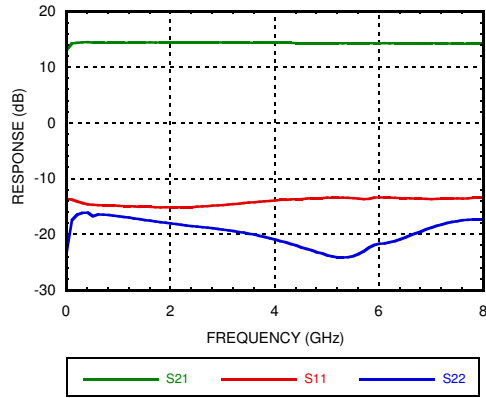
<sup>[1]</sup> Adjust Vgg1 between -2V to 0V to achieve Idd = 400mA typical.

<sup>[2]</sup> Two-Tone Output Power = 0dBm Per Tone , 1 MHz Spacing.

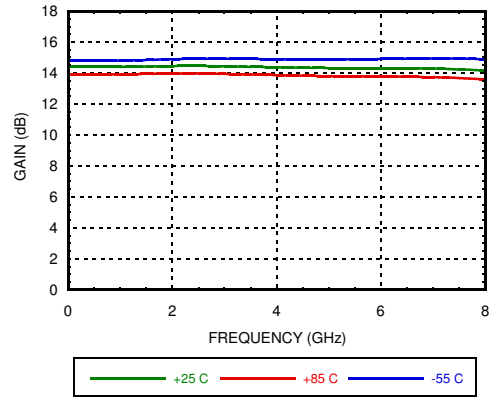


**GaAs MMIC 1 WATT  
POWER AMPLIFIER DC - 6 GHz**

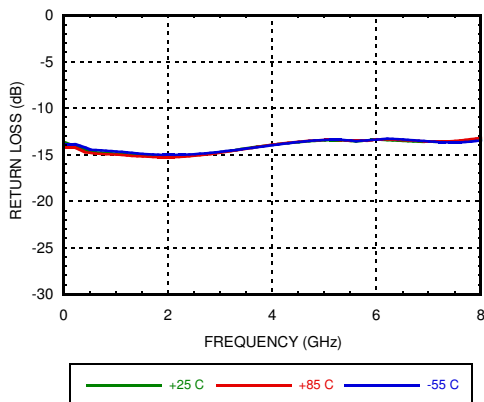
**Broadband Gain & Return Loss**



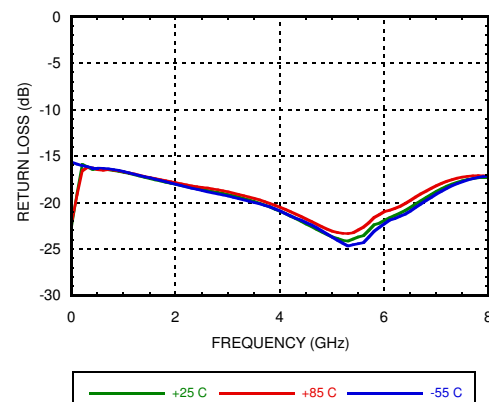
**Gain vs. Temperature**



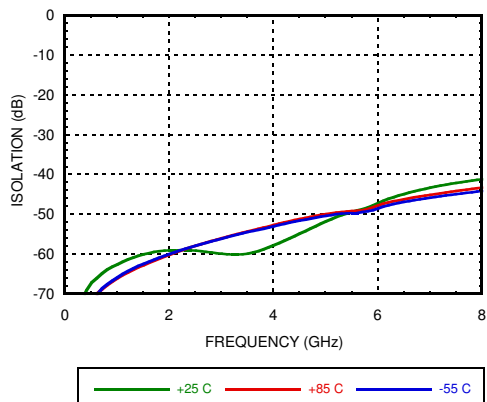
**Input Return Loss vs. Temperature**



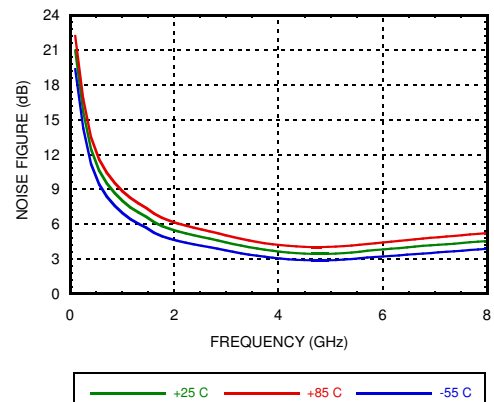
**Output Return Loss vs. Temperature**



**Reverse Isolation vs. Temperature**



**Noise Figure vs. Temperature**

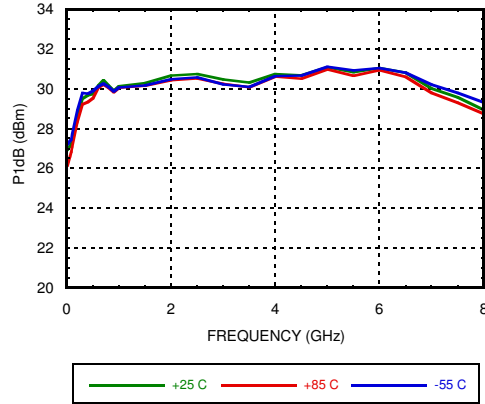




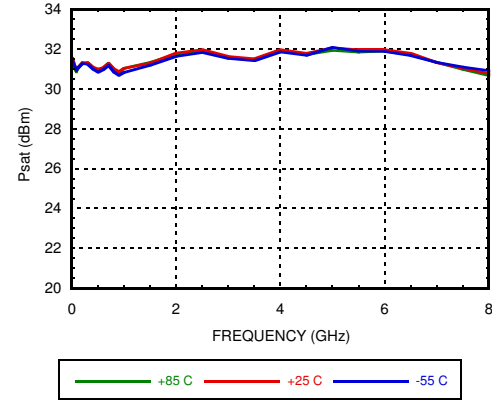
**GaAs MMIC 1 WATT  
POWER AMPLIFIER DC - 6 GHz**

AMPLIFIERS - LINEAR & POWER - CHIP

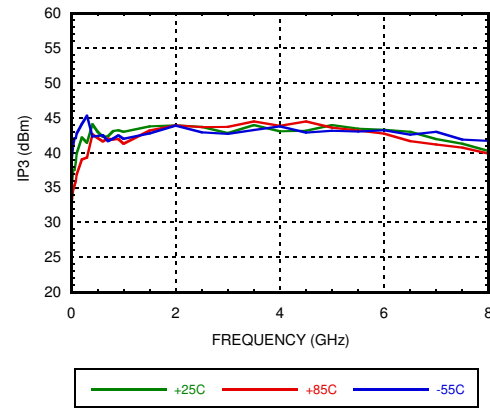
**P1dB vs. Temperature**



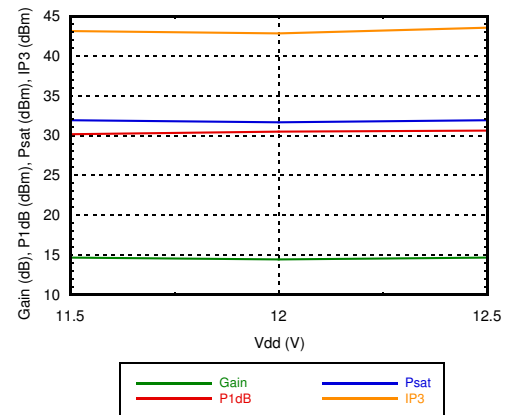
**Psat vs. Temperature**



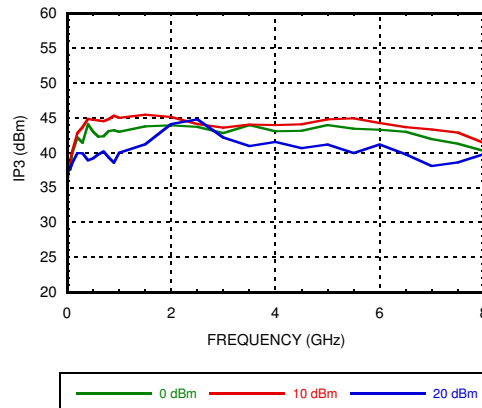
**Output IP3 vs. Temperature**



**Gain, Power & Output IP3 vs. Supply Voltage @ 3 GHz, Fixed Vgg**



**Output IP3 vs. Output Tone Power**



Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106  
Phone: 781-329-4700 • Order online at [www.analog.com](http://www.analog.com)  
Application Support: Phone: 1-800-ANALOG-D


**GaAs MMIC 1 WATT  
POWER AMPLIFIER DC - 6 GHz**
**Absolute Maximum Ratings**

Drain Bias Voltage (Vdd)	+14 Vdc
Gate Bias Voltage (Vgg1)	-3 to 0 Vdc
Gate Bias Voltage (Vgg2)	+4 to +7V
RF Input Power (RFIN)(Vdd = +12V Vdc)	+25 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 95 mW/°C above 85 °C)	5.6 W
Thermal Resistance (channel to die bottom)	10.5 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C
ESD Sensitivity (HBM)	Class 1B

**Typical Supply Current vs. Vdd**

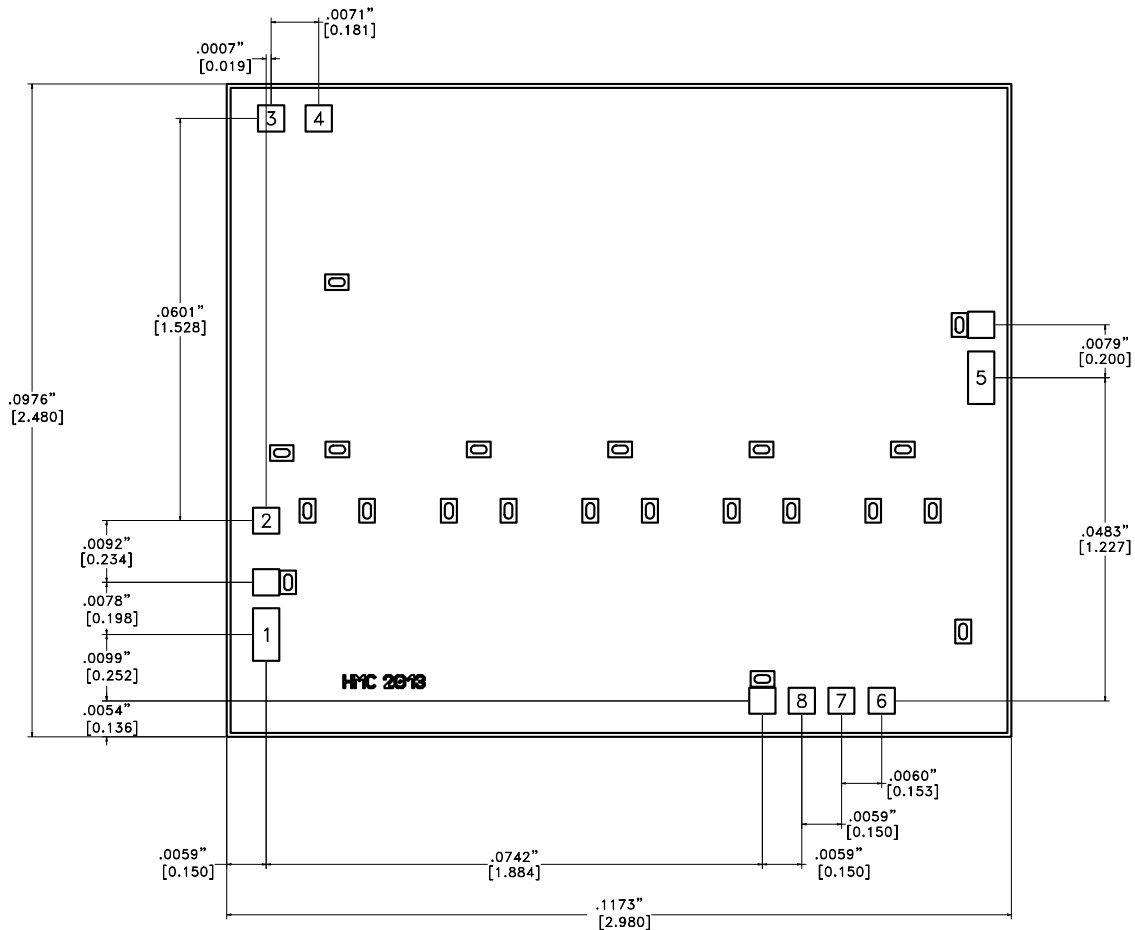
Vdd (V)	Idd (mA)
11.5	375
12.0	400
12.5	430


**ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS**



## GaAs MMIC 1 WATT POWER AMPLIFIER DC - 6 GHz

### Outline Drawing



### Die Packaging Information <sup>[1]</sup>

Standard	Alternate
GP-1 (Gel Pack)	[2]

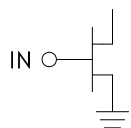
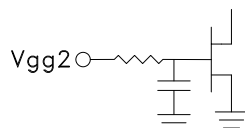
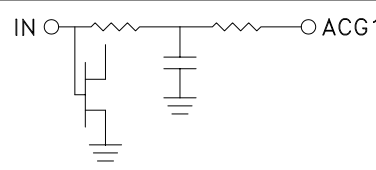
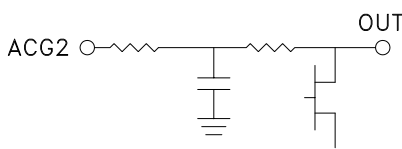
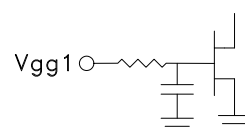

[1] Refer to the "Packaging Information" section for die packaging dimensions.

[2] For alternate packaging information contact Hittite Microwave Corporation.

#### NOTES:

1. ALL DIMENSIONS IN INCHES [MILLIMETERS]
2. DIE THICKNESS IS 0.004 (0.100)
3. TYPICAL BOND PAD IS 0.004 (0.100) SQUARE
4. BOND PAD METALIZATION: GOLD
5. BACKSIDE METALLIZATION: GOLD
6. BACKSIDE METAL IS GROUND
7. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS
8. OVERALL DIE SIZE IS  $\pm .002$

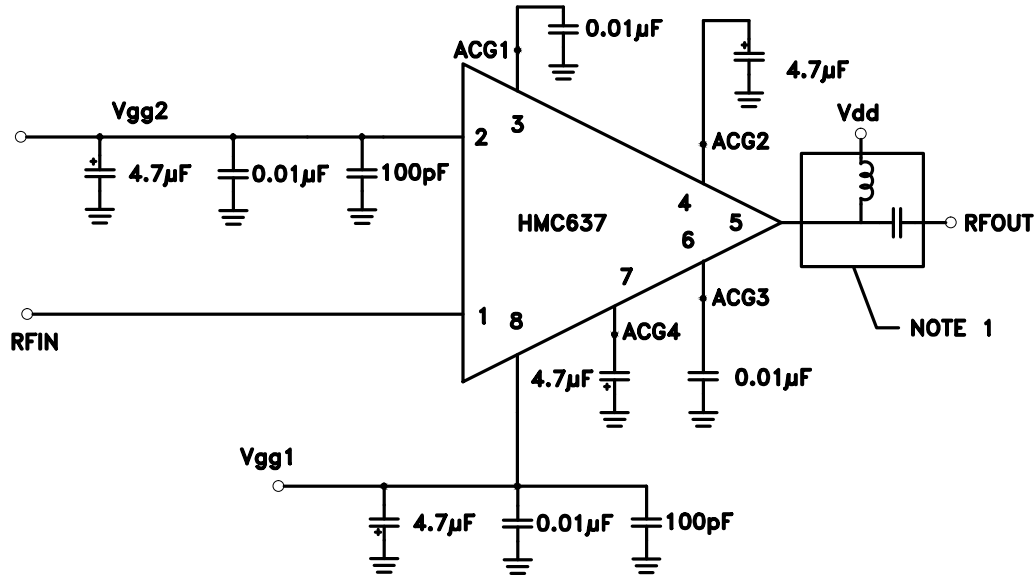

**GaAs MMIC 1 WATT  
POWER AMPLIFIER DC - 6 GHz**
**Pad Descriptions**

Pad Number	Function	Description	Interface Schematic
1	IN	This pad is DC coupled and matched to 50 Ohms. Blocking capacitor is required.	
2	Vgg2	Gate control 2 for amplifier. Attach bypass capacitors per application circuit herein. For nominal operation +6V should be applied to Vgg2.	
3	ACG1	Low frequency termination. Attach bypass capacitor per application circuit herein.	
4	ACG2	Low frequency termination. Attach bypass capacitor per application circuit herein.	
5	OUT & Vdd	RF output for amplifier. Connect DC bias (Vdd) network to provide drain current (Idd). See application circuit herein.	
6, 7	ACG3, ACG4	Low frequency termination. Attach bypass capacitor per application circuit herein.	
8	Vgg1	Gate control 1 for amplifier. Attach bypass capacitors per application circuit herein. Please follow "MMIC Amplifier Biasing Procedure" application note.	
Die Bottom	GND	Die bottom must be connected to RF/DC ground.	



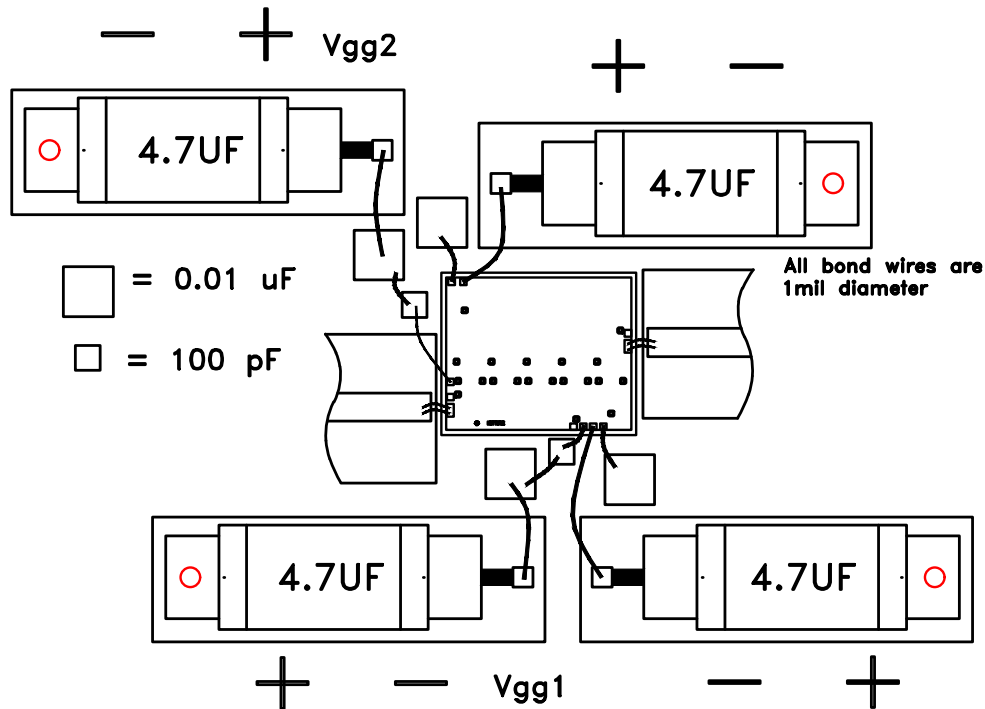
**GaAs MMIC 1 WATT  
POWER AMPLIFIER DC - 6 GHz**

**Application Circuit**



NOTE 1: Drain Bias (Vdd) must be applied through a broadband bias tee with low series resistance and capable of providing 500mA

**Assembly Diagram**





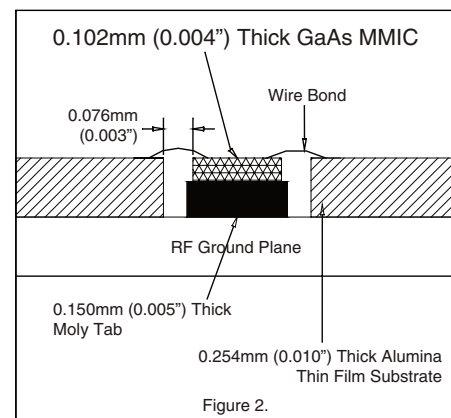
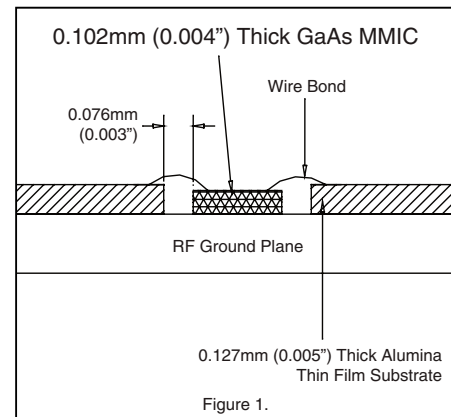
## GaAs MMIC 1 WATT POWER AMPLIFIER DC - 6 GHz

### Mounting & Bonding Techniques for Millimeterwave GaAs MMICs

The die should be attached directly to the ground plane eutectically or with conductive epoxy (see HMC general Handling, Mounting, Bonding Note).

50 Ohm Microstrip transmission lines on 0.127mm (5 mil) thick alumina thin film substrates are recommended for bringing RF to and from the chip (Figure 1). If 0.254mm (10 mil) thick alumina thin film substrates must be used, the die should be raised 0.150mm (6 mils) so that the surface of the die is coplanar with the surface of the substrate. One way to accomplish this is to attach the 0.102mm (4 mil) thick die to a 0.150mm (6 mil) thick molybdenum heat spreader (moly-tab) which is then attached to the ground plane (Figure 2).

Microstrip substrates should be placed as close to the die as possible in order to minimize bond wire length. Typical die-to-substrate spacing is 0.076mm to 0.152 mm (3 to 6 mils).



### Handling Precautions

Follow these precautions to avoid permanent damage.

**Storage:** All bare die are placed in either Waffle or Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a dry nitrogen environment.

**Cleanliness:** Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.

**Static Sensitivity:** Follow ESD precautions to protect against ESD strikes.

**Transients:** Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.

**General Handling:** Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers. The surface of the chip may have fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.

### Mounting

The chip is back-metallized and can be die mounted with AuSn eutectic preforms or with electrically conductive epoxy. The mounting surface should be clean and flat.

**Eutectic Die Attach:** A 80/20 gold tin preform is recommended with a work surface temperature of 255 °C and a tool temperature of 265 °C. When hot 90/10 nitrogen/hydrogen gas is applied, tool tip temperature should be 290 °C. DO NOT expose the chip to a temperature greater than 320 °C for more than 20 seconds. No more than 3 seconds of scrubbing should be performed for attachment.

**Epoxy Die Attach:** Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer's schedule.

### Wire Bonding

RF bonds made with two 1 mil wires are recommended. These bonds should be thermosonically bonded with a force of 40-60 grams. DC bonds of 0.001" (0.025 mm) diameter, thermosonically bonded, are recommended. Ball bonds should be made with a force of 40-50 grams and wedge bonds at 18-22 grams. All bonds should be made with a nominal stage temperature of 150 °C. A minimum amount of ultrasonic energy should be applied to achieve reliable bonds. All bonds should be as short as possible, less than 12 mils (0.31 mm).



Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: [ocean@oceanchips.ru](mailto:ocean@oceanchips.ru)

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А